**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- · Low threshold voltage
- Trench MOSFET technology
- Side wettable flanks for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 1 kV HBM (class H1C)
- AEC-Q101 qualified

## 3. Applications

- · Relay driver
- · High-speed line driver
- Low-side load switch
- Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
$V_{GS}$	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	8	Α
Static characte	eristics			•			
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 8 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	13	16	mΩ

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 1 1 1 1 6	D
2	D	drain		
3	G	gate	2 5	G ←
4	S	source	3 8 4	\ \\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6	S
7	D	drain	(SOT1220)	017aaa255
8	S	source		

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package	<sup>P</sup> ackage							
	Name	Description	Version						
PMPB13XNEA		DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220						

# 7. Marking

### Table 4. Marking codes

Type number	Marking code
PMPB13XNEA	4G

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# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C			30	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]		8	А
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	5	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	32	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[1]	-	1.7	W
		T <sub>sp</sub> = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain d	iode			'		
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	2	Α
ESD maximum	rating			'		
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ		-	1000	V
Avalanche rug	gedness		'	'	'	
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 1.35 A; DUT in avalanche (unclamped)		-	21.3	mJ

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

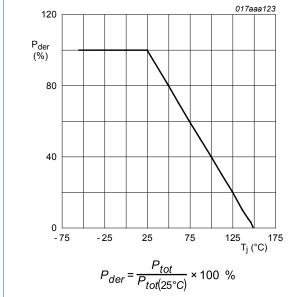


Fig. 1. Normalized total power dissipation as a function of junction temperature

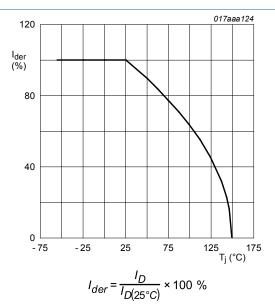


Fig. 2. Normalized continuous drain current as a function of junction temperature

### 30 V, N-channel Trench MOSFET

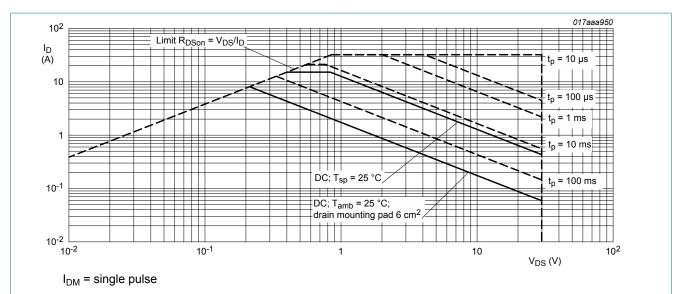


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

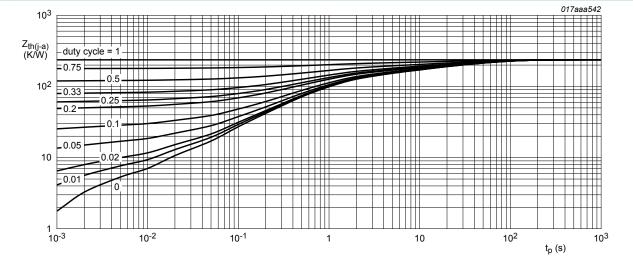
30 V, N-channel Trench MOSFET

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

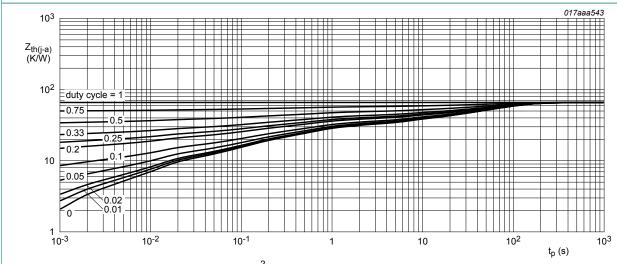
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	in free air	[1]	-	235	270	K/W	
	junction to ambient		[2]	-	67	74	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	5	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm<sup>2</sup>

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = 250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.4	0.65	0.9	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 8 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	13	16	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 8 \text{ A}; T_j = 150 \text{ °C}$	-	21	27	mΩ
		$V_{GS} = 2.5 \text{ V}; I_D = 7.2 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	14	20	mΩ
		V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 3.7 A; T <sub>j</sub> = 25 °C	-	17	24	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 8 \text{ A}; T_j = 25 \text{ °C}$	-	60	-	S
$R_G$	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	-	2.1	-	Ω
Dynamic ch	aracteristics		'			
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 6 A; V <sub>GS</sub> = 4.5 V;	-	24	36	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	2.4	-	nC
$Q_{GD}$	gate-drain charge	1	-	4.6	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	2195	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	155	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	135	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 6 A; V <sub>GS</sub> = 4.5 V;	-	12	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	30	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	54	-	ns
t <sub>f</sub>	fall time		-	49	-	ns
Source-drai	in diode					
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 2 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.6	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 2 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	12	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 15 V; T <sub>j</sub> = 25 °C	-	4	-	nC

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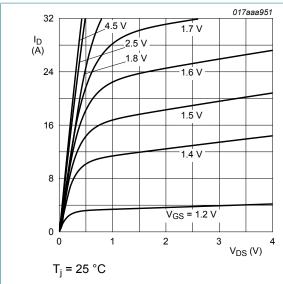
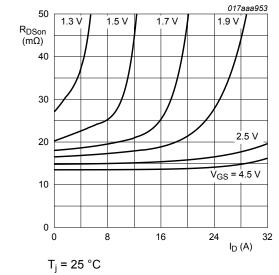
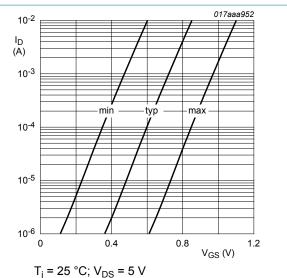


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



Drain-source on-state resistance as a function Fig. 8. of drain current; typical values





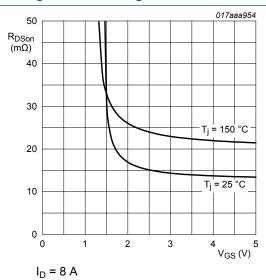


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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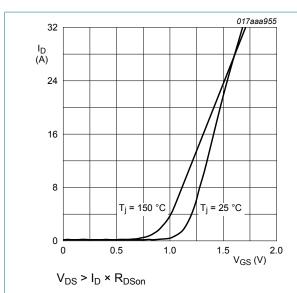


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

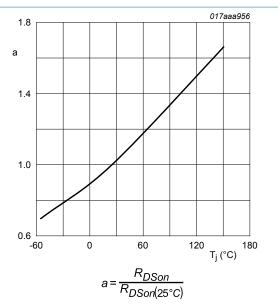


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

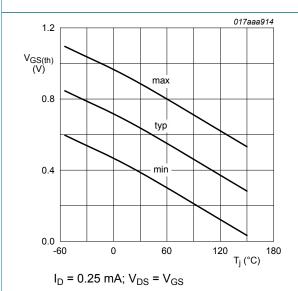


Fig. 12. Gate-source threshold voltage as a function of junction temperature

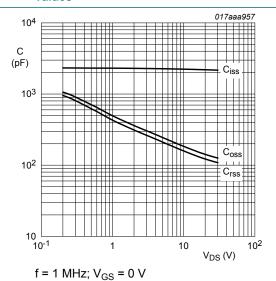


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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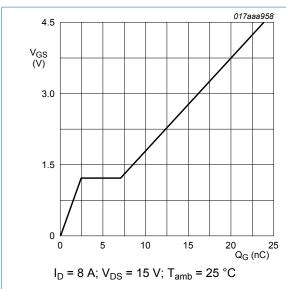


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$ 

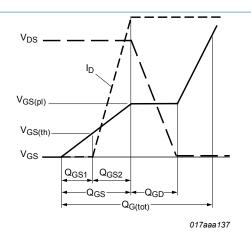


Fig. 15. MOSFET transistor: Gate charge waveform definitions

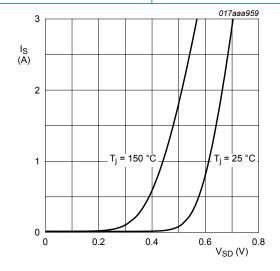
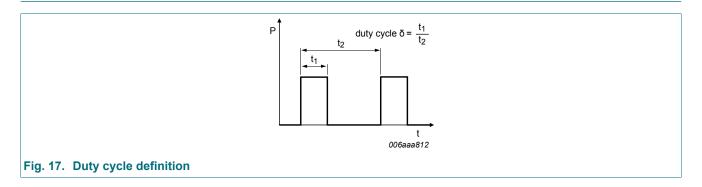


Fig. 16. Source current as a function of source-drain voltage; typical values

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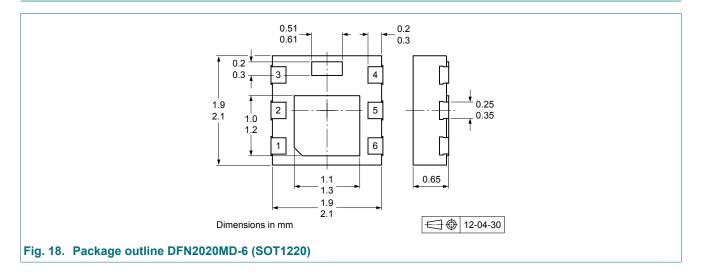
## 11. Test information



## **Quality information**

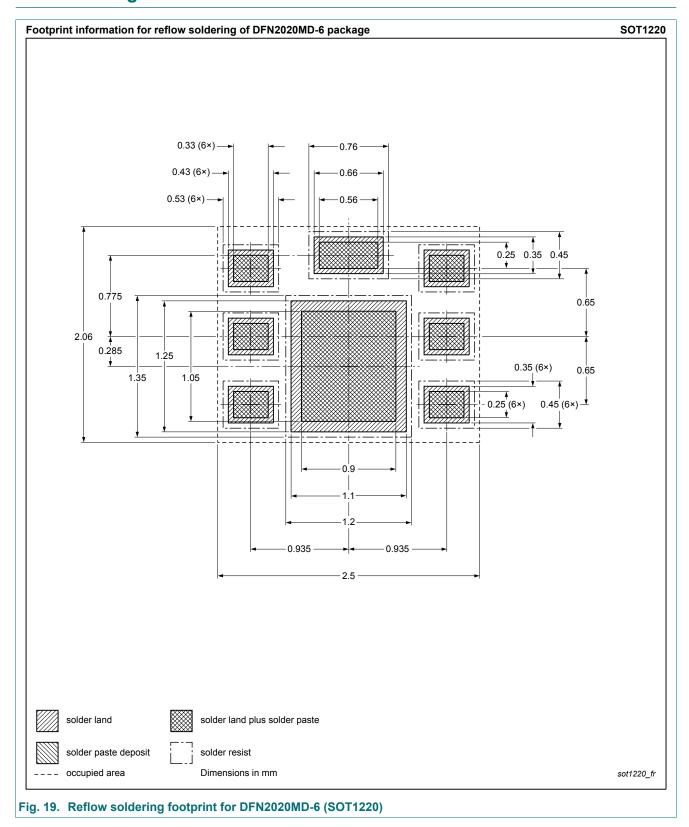
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 12. Package outline



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# 13. Soldering



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# 14. Revision history

### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB13XNEA v.1	20180910	Product data sheet	-	-

#### 30 V, N-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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# PMPB13XNEA

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